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JVSTB

Journal of Vacuum Science and Technology B | 2nd Series | Volume 31, Number 1 | January/February 2013

Nanotechnology & Microelectronics: Materials, Processing, Measurement, & Phenomena

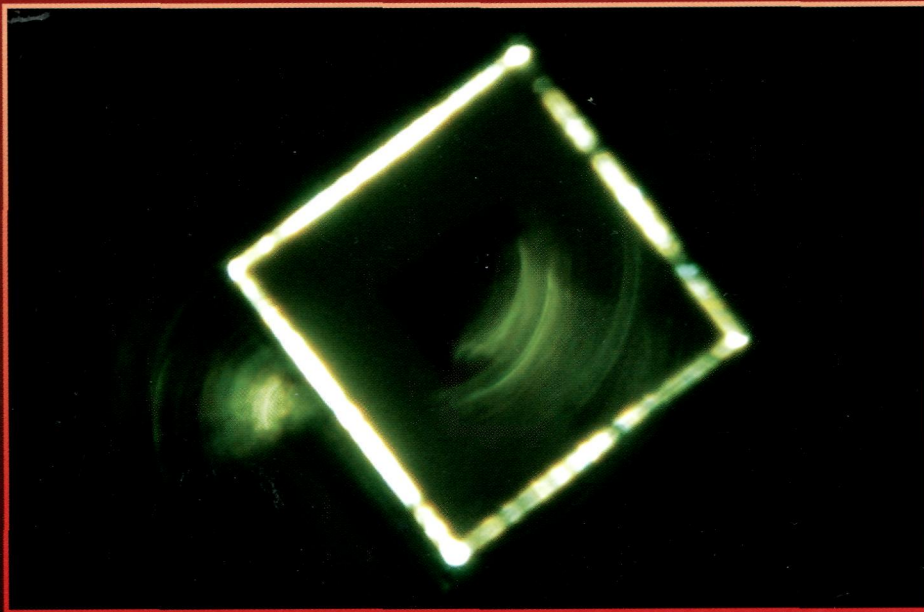


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Papers from the 17th Workshop on Dielectrics in Microelectronics



An AVS journal published by the Society
through the American Institute of Physics

Nanotechnology & Microelectronics:

Materials, Processing, Measurement, and Phenomena

Second Series
Volume 31, Number 1
Jan/Feb 2013

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Journal of Vacuum Science and Technology B Nanotechnology & Microelectronics: Materials, Processing, Measurement & Phenomena (ISSN: 0734-211X) is published six times annually (Jan/Feb, Mar/Apr, May/Jun, Jul/Aug, Sep/Oct, Nov/Dec) by AVS through the American Institute of Physics, Suite 1NO1, 2 Huntington Quadrangle, Melville, NY 11747-4502. Periodicals postage paid at Huntington Station, NY 11746, and at additional mailing offices. 2013 subscription rates are: US\$1720. POSTMASTER: Send address changes to *Journal of Vacuum Science and Technology B Nanotechnology & Microelectronics: Materials, Processing, Measurement & Phenomena*, Membership Services, AVS, 125 Maiden Lane, 15th Floor, New York, NY 10038, membership@avs.org, www.avs.org.

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On The Cover: Scott Newman, Chad Gallinat, Jonathan Wright, Ryan Enck, Anand Sampath, Hongen Shen, Meredith Reed, and Michael Wraback, *JVST B*, 31(1), p. 010601-1 (2013). Cover shows green light emission from a p-side-down, single heterostructure n-InGaN/p-GaN light emitting diode grown by molecular beam epitaxy.